

S/N 08/902,133

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Serial No.: 08/902,133

Filed: July 29, 1997

Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ
ONLY MEMORY DEVICE



Examiner: Valencia Wallace

Group Art Unit: 2815

Docket: 303.356US1

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
AND CERTIFICATION UNDER 1.97(e)(2)**

Assistant Commissioner for Patents
Washington, D.C. 20231

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for review in connection with the above-identified patent application. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, marked as being considered and initialled by the Examiner, be returned with the next official communication.

CERTIFICATION UNDER 37 C.F.R. § 1.97(e)(2)

Pursuant to 37 C.F.R. Section 1.97(e)(2), no item of information contained in the attached Supplemental Information Disclosure Statement and filed herewith was known to any individual designated in 37 C.F.R. Section 1.56 (c) more than three months prior to the filing of this Statement, to the best knowledge of the undersigned on this certification after making reasonable inquiry.

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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Page 2

Dkt: 303.356US1

Applicants respectfully request consideration of these references during prosecution of the above-identified matter.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

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Minneapolis, MN 55402

(612) 373-6973

Date

5/14/99

By

Robert E. Mates
Reg. No. 35,271

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Assistant Commissioner of Patents, Washington, D.C. 20231 on May 14, 1999.

Name

JANA OTTMAR

Signature

Jana A. Ottmar

S/N 08/902,133

PATENT

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Applicant: Leonard Forbes et al.

Examiner: Valencia Wallace

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Title: DYNAMIC ELECTRICAL ERASABLE PROGRAMMABLE READ
ONLY MEMORY DEVICE



COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

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Assistant Commissioner for Patents
Washington, D.C. 20231

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Applicants would like to bring to the Examiner's attention the following list of co-pending applications for the above-identified patent application.

Serial No.	Filing Date	Attorney Docket No.	Title
08/903,452	07/29/97	303.324US1	Transistor with Variable Electron Affinity Gate and Methods of Fabrication and Use
09/256,643	02/23/99	303.324US2	Transistor with Variable Electron Affinity Gate and Methods of Fabrication and Use
08/903,486	07/29/97	303.326US1	Silicon Carbide Gate Transistor and Fabrication Process
09/259,870	03/01/99	303.326US2	Silicon Carbide Gate Transistor and Fabrication Process
09/138,294	08/21/98	303.353US2	Transistor with Silicon Oxycarbide Gate and Methods of Fabrication
08/902,843	07/29/97	303.354US1	DEAPROM Having Amorphous Silicon Carbide Gate Insulator
09/135,413	08/14/98	303.354US2	DEAPROM Having Amorphous Silicon Carbide Gate Insulator
09/134,713	08/14/98	303.354US3	DEAPROM Having Amorphous Silicon Carbide Gate Insulator

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Page 2
Dkt: 303.356US1

Filing Date: July 29, 1997

Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE

Serial No.	Filing Date	Attorney Docket No.	Title
08/902,098	07/29/97	303.355US1	DEAPROM and Transistor with Gallium Nitride or Gallium Aluminum Nitride Gate
09/140,978	08/27/98	303.355US2	DEAPROM and Transistor with Gallium Nitride or Gallium Aluminum Nitride Gate
09/141,392	08/27/98	303.355US3	DEAPROM and Transistor with Gallium Nitride or Gallium Aluminum Nitride Gate
08/903,453	07/29/97	303.378US1	Carbonized Silicon Gate Insulators for Integrated Circuits
09/258,467	02/26/99	303.378US2	Carbonized Silicon Gate Insulators for Integrated Circuits

Respectfully submitted,

LEONARD FORBES ET AL.

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Date

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Robert E. Mates
Reg. No. 35,271

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Assistant Commissioner of Patents, Washington, D.C. 20231 on May 11, 1999.

Name

JANA OTTMAR

Signature

Jana A. Ottmar